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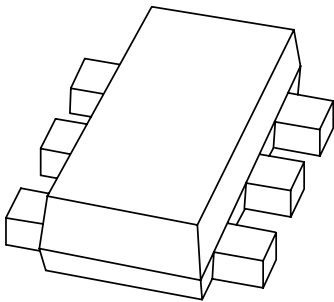
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PMEG2010EV

Low V_F MEGA Schottky barrier diode

Product data sheet
Supersedes data of 2002 Jun 24

2003 Aug 20

Low V_F MEGA Schottky barrier diode

PMEG2010EV

FEATURES

- Forward current: 1 A
- Reverse voltage: 20 V
- Very low forward voltage
- Ultra small SMD package
- Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

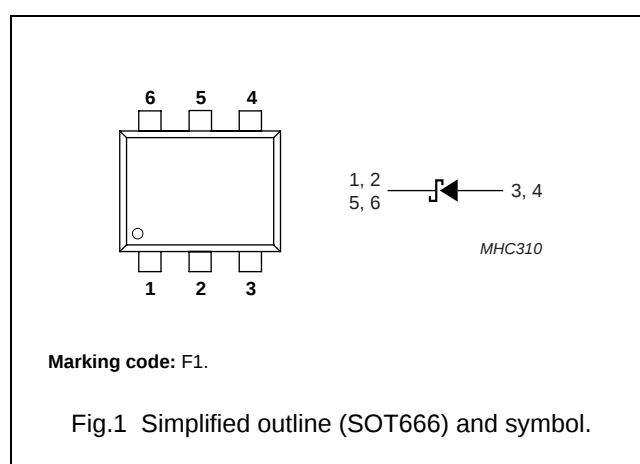
- Low voltage rectification
- High efficiency DC/DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection in a SOT666 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current		–	1	A
I_{FSM}	non-repetitive peak forward current	$t = 8.3$ ms half sinewave; JEDEC method; note 1	–	8	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	125	°C
T_{amb}	operating ambient temperature		–65	+125	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

Low V_F MEGA Schottky barrier diode

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W

Notes

1. Refer to SOT666 standard mounting conditions.
2. Mounted on printed circuit-board, 1 cm² copper area.

Soldering

The only recommended soldering method is reflow soldering.

ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	continuous forward voltage	$I_F = 10\text{ mA}$	240	270	mV
		$I_F = 100\text{ mA}$	300	350	mV
		$I_F = 1000\text{ mA}$; note 1; see Fig.2	480	550	mV
I_R	reverse current	$V_R = 5\text{ V}$; note 2	5	10	μA
		$V_R = 8\text{ V}$; note 2	7	20	μA
		$V_R = 15\text{ V}$; note 2; see Fig.3	10	50	μA
C_d	diode capacitance	$V_R = 5\text{ V}$; $f = 1\text{ MHz}$; see Fig.4	19	25	pF

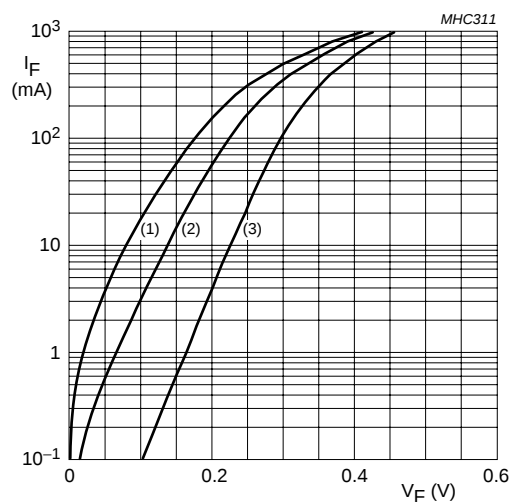
Notes

1. Only valid if pins 1, 2, 5 and 6 are soldered on a 1 cm² copper solder land.
2. Pulse test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.

Low V_F MEGA Schottky barrier diode

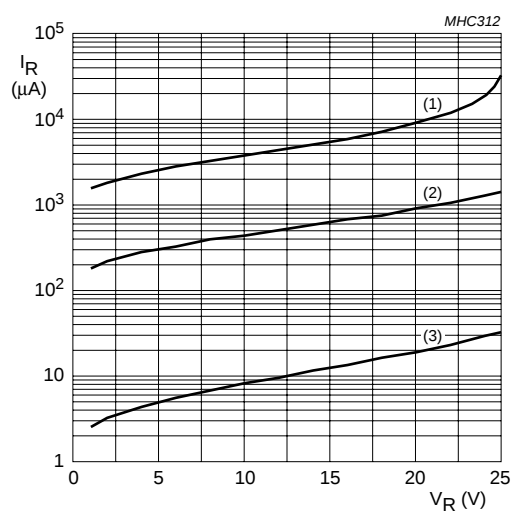
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GRAPHICAL DATA



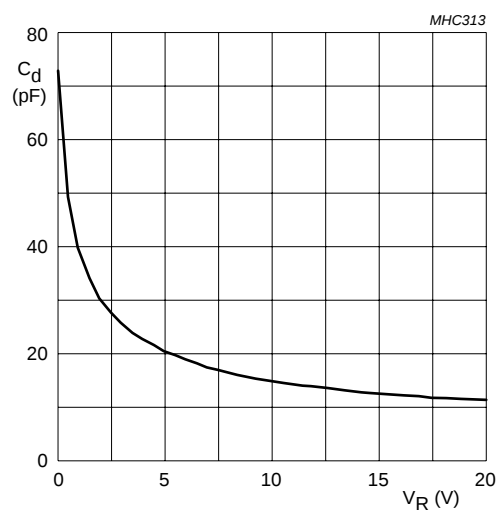
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



$f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

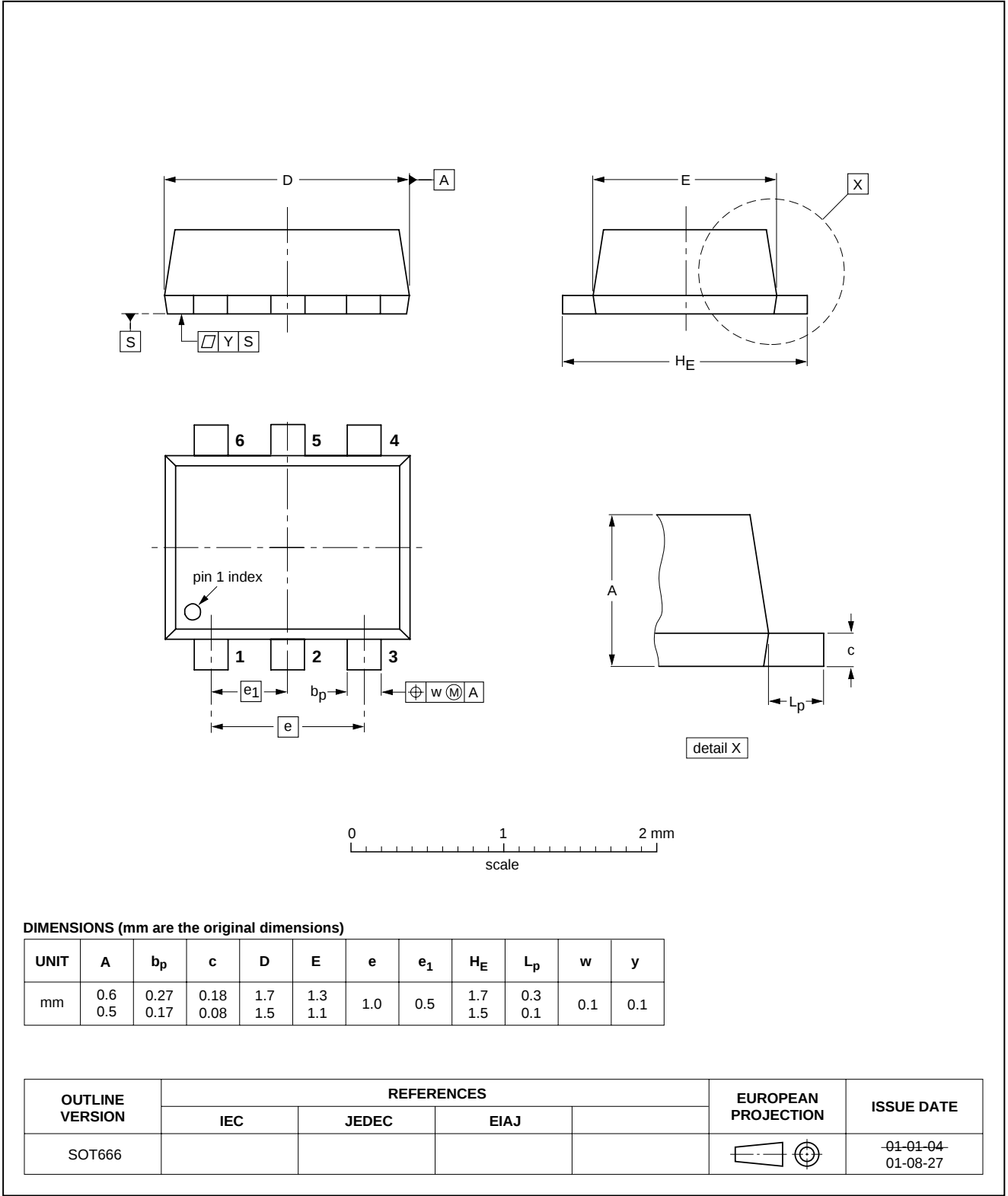
Low V_F MEGA Schottky barrier diode

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



Low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: **<http://www.nxp.com>**

For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

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